



100V 175°C PNP LOW SAT HIGH POWER TRANSISTOR IN POWERDI5060-8

Features

- $BV_{CEO} > -100V$
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- $R_{CE(SAT)} = 110m\Omega$ (typ)
- Rated to +175°C—Ideal for High Ambient Temperature **Environments**
- Complementary Part DXTN3C100PS
- Meets Requirements of Automotive Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

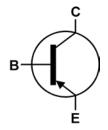
Mechanical Data

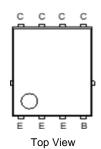
- Case: Power®DI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

Applications

- **Power Management**
- Load Switch
- Linear Mode Voltage Regulator
- **Backlighting Applications**







Pin Configuration

Bottom View

Internal Schematic

Ordering Information

Top View

| Ī | Product | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity per Reel |
|---|-----------------|------------|-------------|--------------------|-----------------|-------------------|
| | DXTP3C100PSQ-13 | Automotive | DXTP3C100PS | 13 | 12 | 2500 |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

Marking Information



DXTP3 = Product Type Marking Code C100PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | -100 | V |
| Collector-Emitter Voltage | V _{CEO} | -100 | V |
| Emitter-Base Voltage | V _{EBO} | -7 | V |
| Base Current | I _B | -0.5 | А |
| Continuous Collector Current | Ic | -3 | Α |
| Peak Pulse Collector Current | I _{CM} | -8 | Α |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|-----------------------------------|------------------|------|------|--|
| Power Dissipation | (Note 5) | P _D | 5 | W | |
| Thermal Decistance, Junetian to Ambient | (Note 5) | Б | 40 | °C/W | |
| Thermal Resistance, Junction to Ambient | (Note 6) | $R_{\Theta JA}$ | 120 | | |
| Thermal Decistance, Junetica to Cons | (Note 5, 7) | Б | 2 | °C/W | |
| Thermal Resistance, Junction to Case | (Note 6, 7) | R _{eJC} | 12 | | |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +175 | °C | | |

ESD Ratings (Note 8)

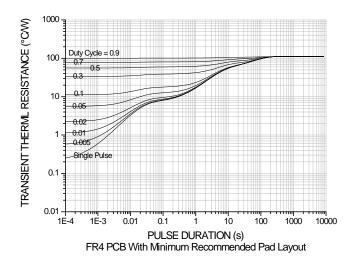
| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge—Human Body Model | ESD HBM | V0008 | V | 3A |
| Electrostatic Discharge—Machine Model | ESD MM | 400V | V | С |

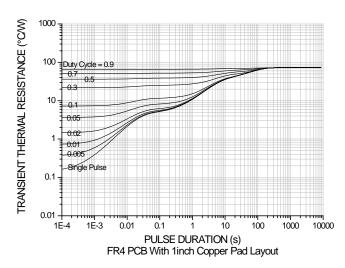
Notes:

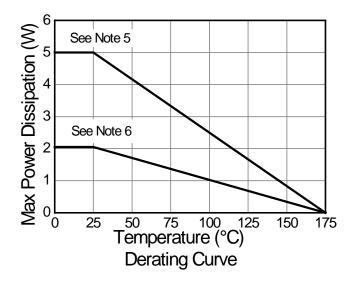
- 5. For a device mounted with the collector lead on 25mm × 25mm 2oz copper, on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions while operating in a steady state.
- 6. Same as Note 5 except mounted on minimum recommended pad layout.
- 7. Thermal resistance from junction to the top of the case.
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Typical Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)









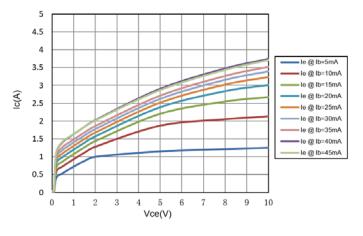
Electrical Characteristics (@ $T_A = \pm 25^{\circ}C$, unless otherwise specified.)

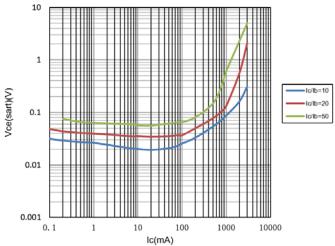
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|----------------------|------|-------|------|------|---|
| OFF CHARACTERISTICS | | | | | | |
| Collector-Base Breakdown Voltage | | -100 | _ | _ | > | I _C = -100μA |
| Collector-Emitter Breakdown Voltage (Note 9) | | -100 | _ | _ | ٧ | $I_C = -10mA$ |
| Emitter-Base Breakdown Voltage | BV _{EBO} | -7 | _ | _ | > | $I_E = -100 \mu A$ |
| Collector-Base Cutoff Current | I _{CBO} | _ | _ | -100 | nA | V _{CB} = -80V |
| Collector-base Cuton Current | | _ | _ | -50 | μΑ | V _{CB} = -80V @Tj = 150°C |
| Emitter Cutoff Current | I _{EBO} | _ | _ | -100 | nA | V _{EB} = -7V |
| Collector-Emitter Cutoff Current | I _{CES} | _ | _ | -100 | nA | V _{CES} = -80V |
| ON CHARACTERISTICS (Note 9) | | | | | | |
| | | 170 | 305 | _ | _ | I _C = -500mA, V _{CE} = -10V |
| DC Current Gain | h | 160 | 275 | _ | | $I_C = -1A$, $V_{CE} = -10V$ |
| DC Curient Gain | h _{FE} | 45 | 90 | _ | | $I_C = -2A$, $V_{CE} = -10V$ |
| | | 10 | 20 | _ | | $I_C = -3A$, $V_{CE} = -10V$ |
| Collector-Emitter Saturation Voltage | \/· . | _ | -70 | -110 | mV | $I_C = -0.5A, I_B = -50mA$ |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | _ | -220 | -360 | | $I_C = -2A$, $I_B = -200mA$ |
| Collector-Emitter Saturation Resistance | R _{CE(sat)} | _ | 110 | 180 | mΩ | $I_C = -2A$, $I_B = -200mA$ |
| Base-Emitter Saturation Voltage | V _{BE(sat)} | _ | -0.91 | -1 | ٧ | $I_C = -1A$, $I_B = -50mA$ |
| Base-Emilier Saturation voltage | | _ | -1.02 | -1.2 | | $I_C = -2A$, $I_B = -200mA$ |
| Base-Emitter Turn-On Voltage | V _{BE(on)} | _ | -0.68 | -0.9 | > | $I_C = -0.1A, V_{CE} = -2V$ |
| SMALL SIGNAL CHARACTERISTICS | | | | | | |
| Current Gain-Bandwidth Product | f _T | _ | 125 | _ | MHz | $V_{CE} = -10V, I_{C} = -100mA, f = 100MHz$ |
| Output Capacitance | C _{obo} | _ | 30 | _ | pF | $V_{CB} = -10V$, $f = -1MHz$ |
| Delay Time | t _d | _ | 20 | _ | ns | |
| Rise Time | | _ | 180 | _ | ns | |
| Turn-On Time | | _ | 200 | _ | ns | $V_{CC} = -12.5V, I_{C} = -1A$ |
| Storage Time | | _ | 350 | _ | ns | $I_{B1} = -I_{B2} = 50 \text{mA}$ |
| Fall Time | | _ | 220 | _ | ns | |
| Turn-Off Time | | _ | 570 | _ | ns | |

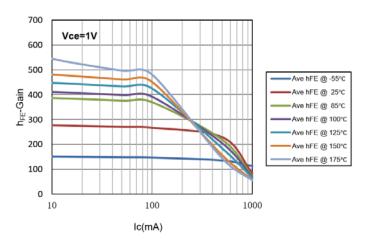
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

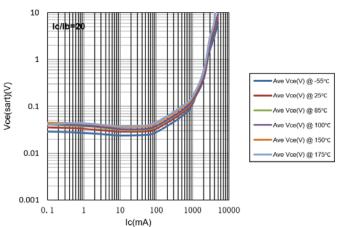


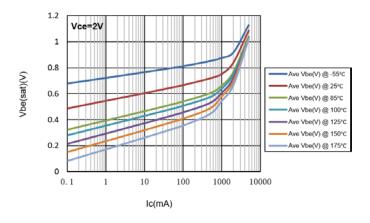
Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

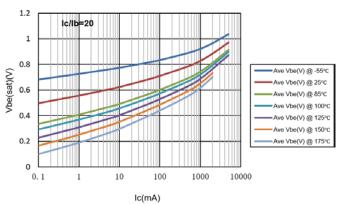












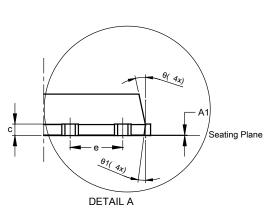


Package Outline Dimensions

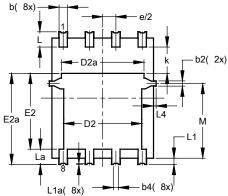
Please see http://www.diodes.com/package-outlines.html for the latest version.

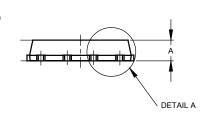
Ø0.986 Depth 0.07±0.030

1.900 1.400 E1 E



PowerDI5060-8 (SWP) (Type Q)



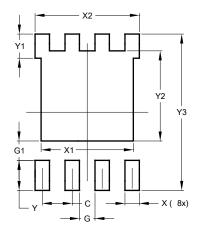


| PowerDI5060-8 (SWP) | | | | | | |
|----------------------|----------|---------|-------|--|--|--|
| | (Type Q) | | | | | |
| Dim | Min | Max | Тур | | | |
| Α | 0.90 | 1.10 | 1.00 | | | |
| A1 | 0 | 0.05 | _ | | | |
| b | 0.30 | 0.50 | 0.41 | | | |
| b2 | 0.20 | 0.35 | 0.25 | | | |
| b4 | |).25REF | - | | | |
| C | 0.230 | 0.330 | 0.277 | | | |
| D | • | .15 BS0 |) | | | |
| D1 | 4.70 | 5.10 | 4.90 | | | |
| D2 | 3.56 | 3.96 | 3.76 | | | |
| D2a | 3.78 | 4.18 | 3.98 | | | |
| Е | 6 | .40 BS0 |) | | | |
| E1 | 5.60 | 6.00 | 5.80 | | | |
| E2 | 3.46 | 3.86 | 3.66 | | | |
| E2a | 4.195 | 4.595 | 4.395 | | | |
| е | 1 | .27BSC |) | | | |
| k | 1.05 | _ | _ | | | |
| L | 0.635 | 0.835 | 0.735 | | | |
| La | 0.635 | 0.835 | 0.735 | | | |
| L1 | 0.200 | 0.400 | 0.300 | | | |
| L1a | 0.050REF | | | | | |
| L4 | 0.025 | 0.225 | 0.125 | | | |
| М | 3.205 | 4.005 | 3.605 | | | |
| θ | 10° | 12° | 11° | | | |
| θ1 | 6° 8° 7° | | | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



| Dimensions | Value (in mm) | | |
|------------|------------------|--|--|
| С | 1.270 | | |
| G | 0.660 | | |
| G1 | 0.820 | | |
| Х | 0.610 | | |
| X1 | 4.100 | | |
| X2 | 4.420 | | |
| Υ | 1.270 | | |
| Y1 | 1.020 | | |
| Y2 | 3.810 | | |
| Y3 | 6.610 | | |

June 2018

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